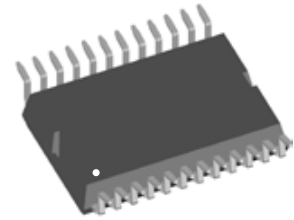
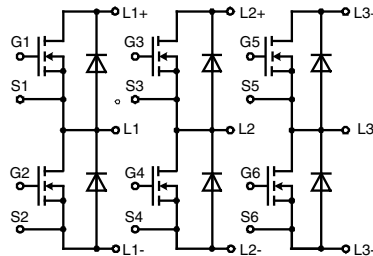


Three phase full Bridge

with Trench MOSFETs
in DCB isolated high current package

$V_{DSS} = 40\text{ V}$
 $I_{D25} = 180\text{ A}$
 $R_{DSon\text{ typ.}} = 1.9\text{ m}\Omega$

Preliminary data



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	40	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^{\circ}\text{C}$	180	A
I_{D90}	$T_C = 90^{\circ}\text{C}$	136	A
I_{D110}	$T_C = 110^{\circ}\text{C}$	120	A
I_{F25}	$T_C = 25^{\circ}\text{C}$ (diode)	182	A
I_{F90}	$T_C = 90^{\circ}\text{C}$ (diode)	112	A
I_{F110}	$T_C = 110^{\circ}\text{C}$ (diode)	88	A

Applications

- AC drives
- in automobiles
 - electric power steering
 - starter generator
 - in industrial vehicles
 - propulsion drives
 - fork lift drives
 - in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Symbol	Conditions	Characteristic Values				
		$(T_{VJ} = 25^{\circ}\text{C}, \text{ unless otherwise specified})$				
		min.	typ.	max.		
$R_{DSon}^{1)}$	on chip level at } $V_{GS} = 10\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.9	2.5	$\text{m}\Omega$
		$T_{VJ} = 125^{\circ}\text{C}$		2.8	5.3	$\text{m}\Omega$
$V_{GS(th)}$	$V_{DS} = 20\text{ V}; I_D = 1\text{ mA}$	2.5		4.5	V	
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0\text{ V}$			5	μA	
			50		μA	
I_{GSS}	$V_{GS} = \pm 20\text{ V}; V_{DS} = 0\text{ V}$			0.2	μA	
Q_g	} $V_{GS} = 10\text{ V}; V_{DS} = 20\text{ V}; I_D = 100\text{ A}$		110		nC	
Q_{gs}			33		nC	
Q_{gd}			30		nC	
$t_{d(on)}$	} inductive load $V_{GS} = +10/0\text{ V}; V_{DS} = 15\text{ V}$ $I_D = 135\text{ A}; R_G = 39\ \Omega;$ $T_J = 125^{\circ}\text{C}$		150		ns	
t_r			240		ns	
$t_{d(off)}$			350		ns	
t_f			170		ns	
E_{on}			0.12		mJ	
E_{off}		0.51		mJ		
E_{recoff}		0.003		mJ		
R_{thJC}	with heat transfer paste (IXYS test setup)			1.0	K/W	
R_{thJH}			1.3	1.6	K/W	

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + R_{Pin\text{ to Chip}})$

Source-Drain Diode

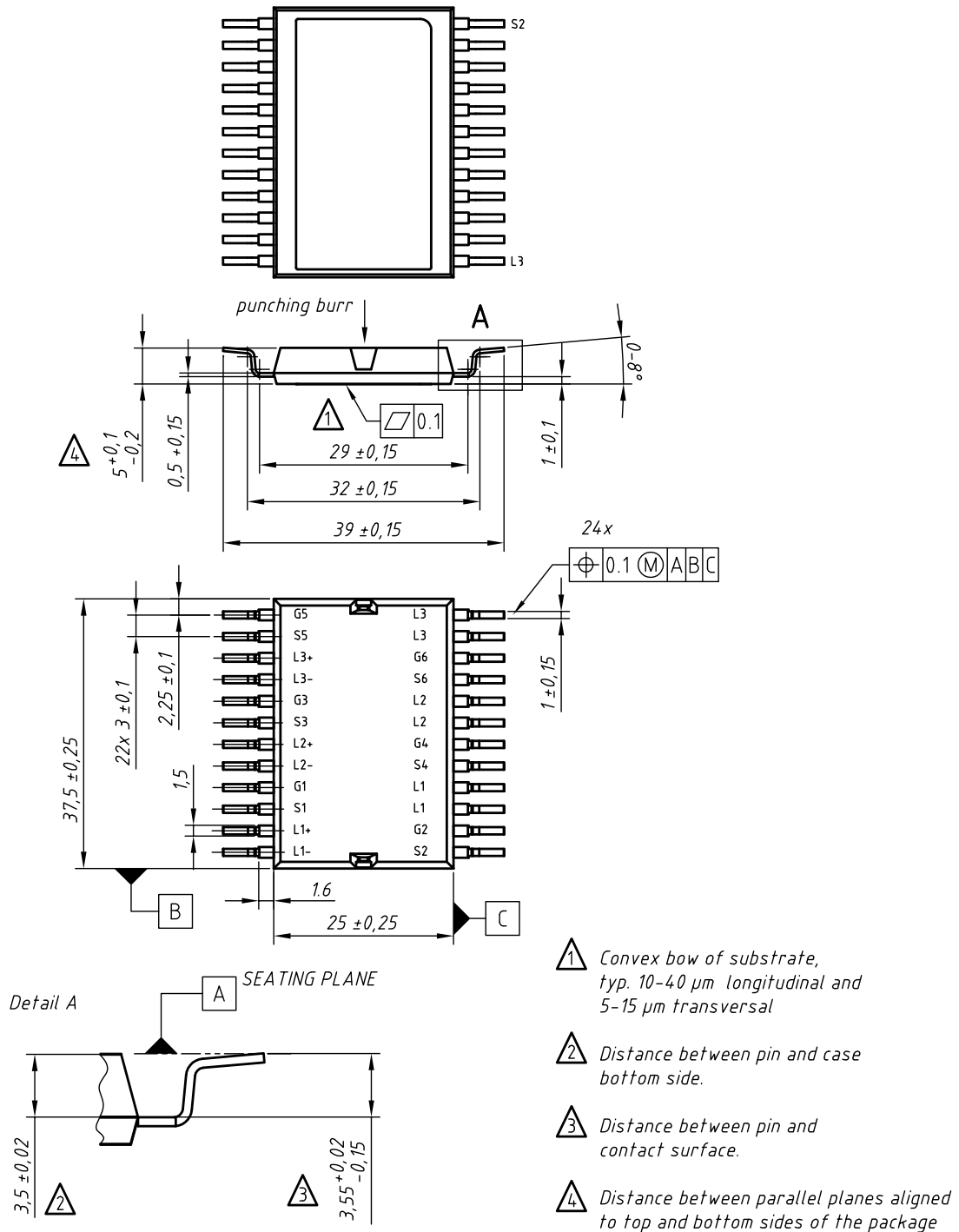
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
($T_J = 25^\circ\text{C}$, unless otherwise specified)					
V_{SD}	(diode) $I_F = 100\text{ A}$; $V_{GS} = 0\text{ V}$	0.9	1.2		V
t_{rr}	} $I_F = 100\text{ A}$; $-di_F/dt = 600\text{ A}/\mu\text{s}$ $V_R = 15\text{ V}$; $T_J = 125^\circ\text{C}$		38		ns
Q_{RM}			0.31		μC
I_{RM}			14		A

Component

Symbol	Conditions	Maximum Ratings		
I_{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections 2 pins for output L1, L2, L3	75		A
T_J		-55...+175		$^\circ\text{C}$
T_{stg}		-55...+125		$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}$, 50/60 Hz, $f = 1\text{ minute}$	1000		V~
F_C	mounting force with clip	50 - 250		N

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
$R_{pin\ to\ chip}^{1)}$	L+ to L1/L2/L3 or L- to L1/L2/L3		0.9		$\text{m}\Omega$
C_P	coupling capacity between shorted pins and back side metallization		160		μF
Weight			25		g

¹⁾ $V_{DS} = I_D \cdot (R_{DS(on)} + R_{Pin\ to\ Chip})$

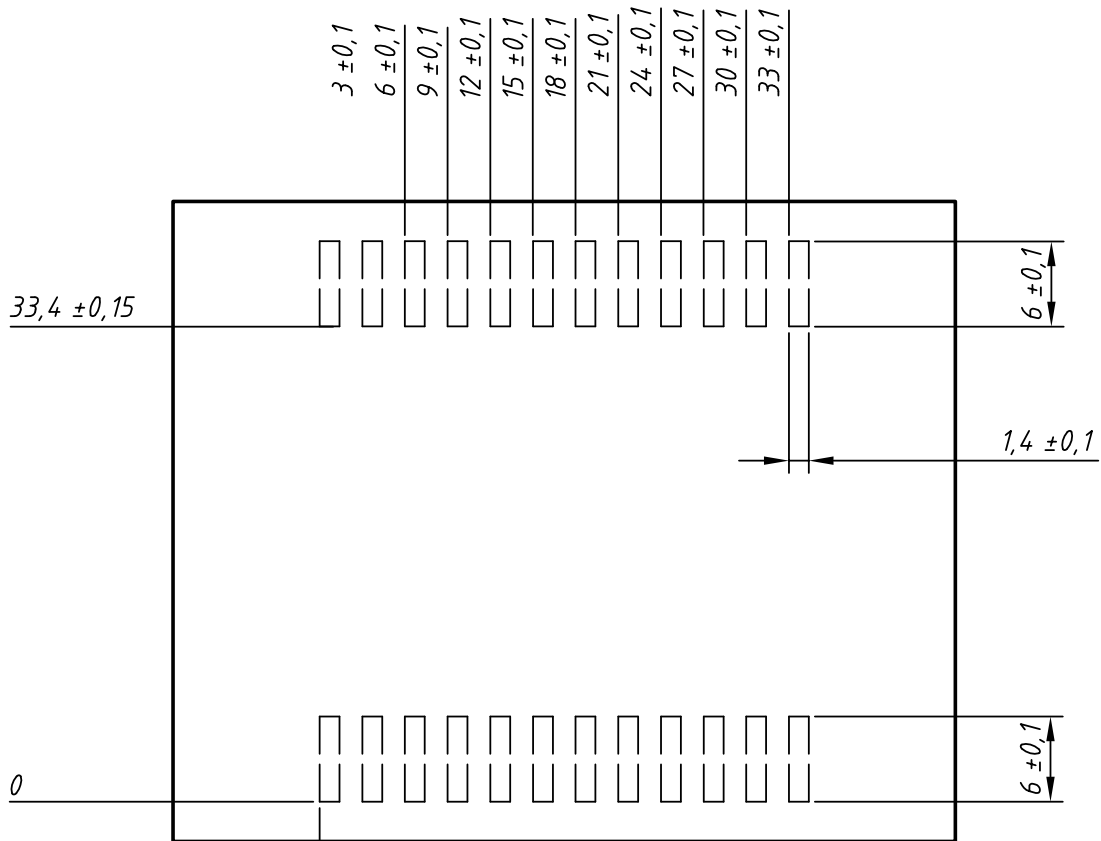


contact pin:
 - galv. tin plating, per pin side: Sn $10...25 \mu\text{m}$, undercoating Ni $0,2...1 \mu\text{m}$
 - stamping edges may be free of tin
 - punching burr: $\leq 0,05\text{mm}$

Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
SMD	Standard	GMM 3x180-004X2 - SMD	GMM 3x180-004X2	Blister	28	509042

IXYS reserves the right to change limits, test conditions and dimensions.

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Remarks:

- 1) pin layout / dimensions are conditionally
- 2) soldering paste thickness: 200µm

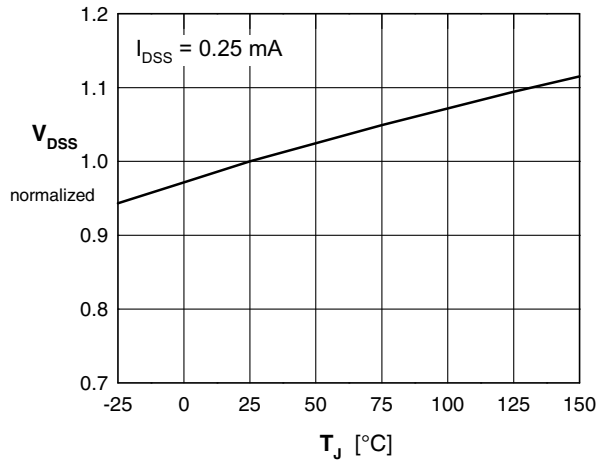


Fig. 1 Drain source breakdown voltage V_{DSS} vs. junction temperature T_{VJ}

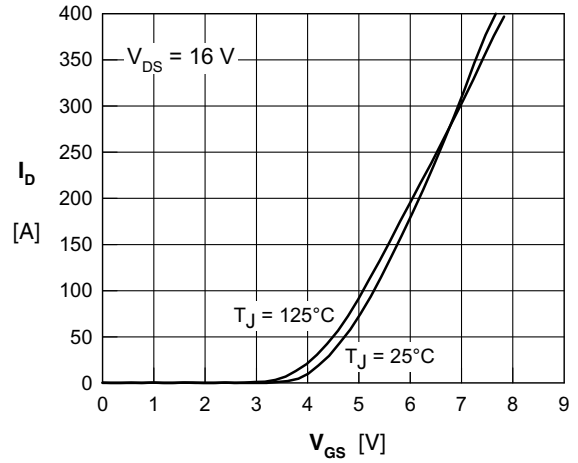


Fig. 2 Typical transfer characteristic

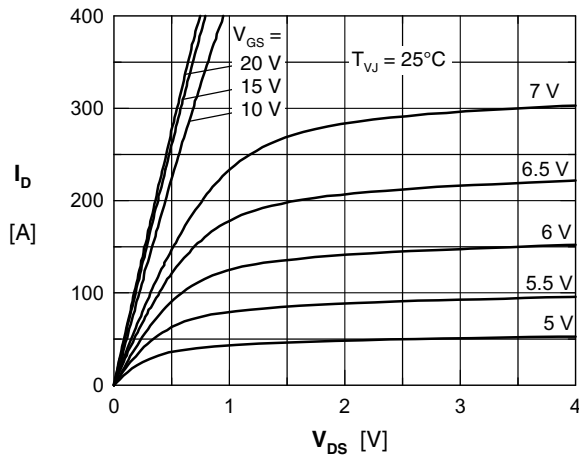


Fig. 3 Typical output characteristic

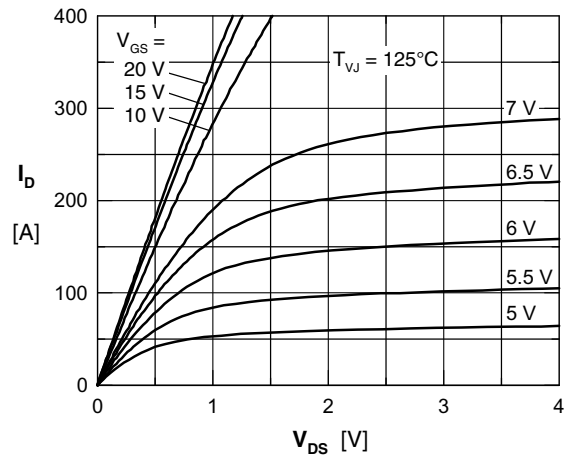


Fig. 4 Typical output characteristic

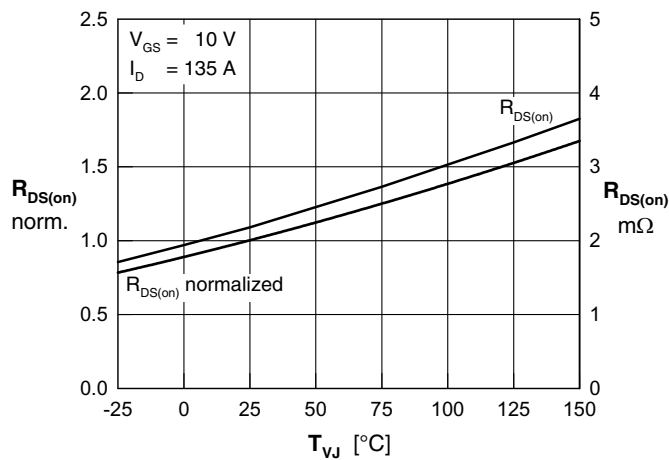


Fig. 5 Typ. drain source on-state resistance $R_{DS(on)}$ versus junction temperature T_J

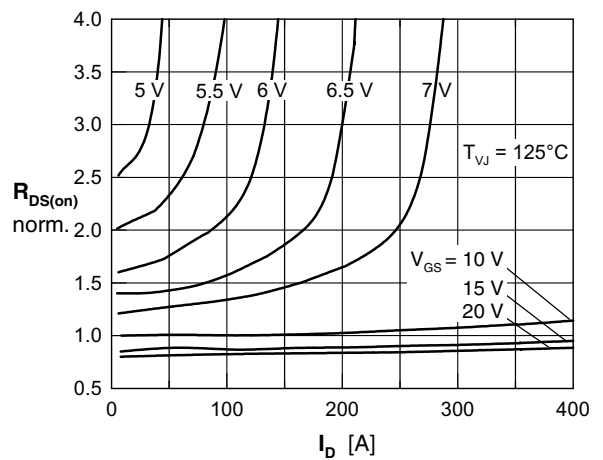


Fig. 6 Typ. drain source on-state resistance $R_{DS(on)}$ versus I_D

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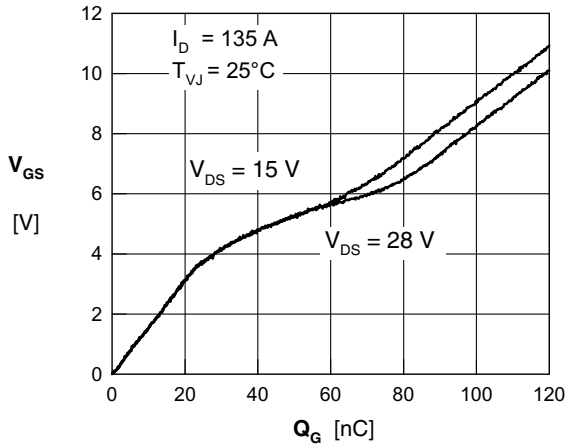


Fig. 7 Gate charge characteristics

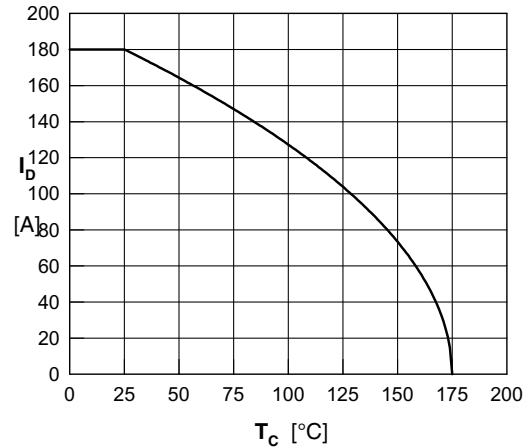
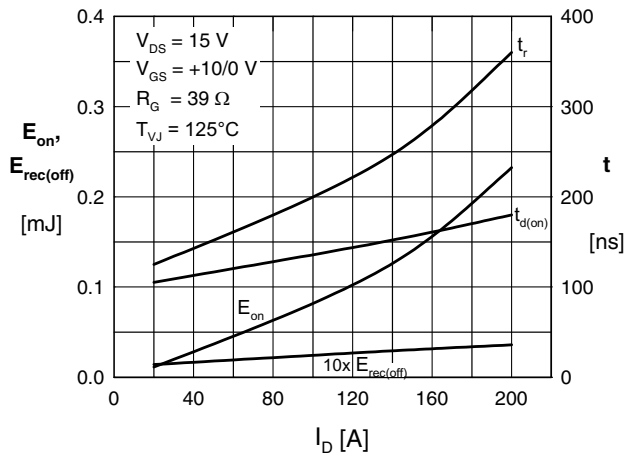

 Fig. 8 Drain current I_D vs. temperature T_C


Fig. 9 Typ. turn-on energy & switching times vs. collector current, inductive switching

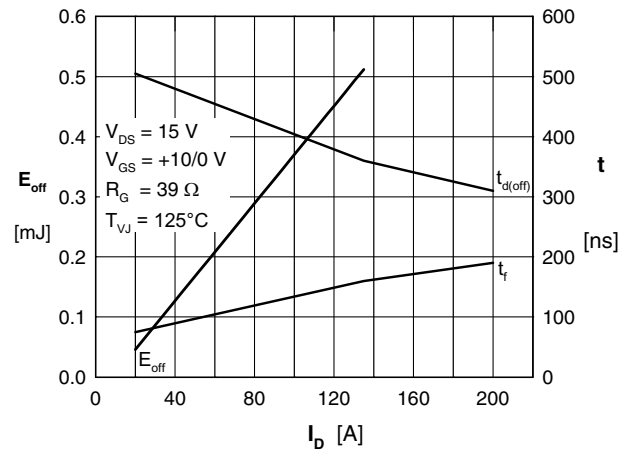


Fig. 10 Typ. turn-off energy & switching times vs. collector current, inductive switching

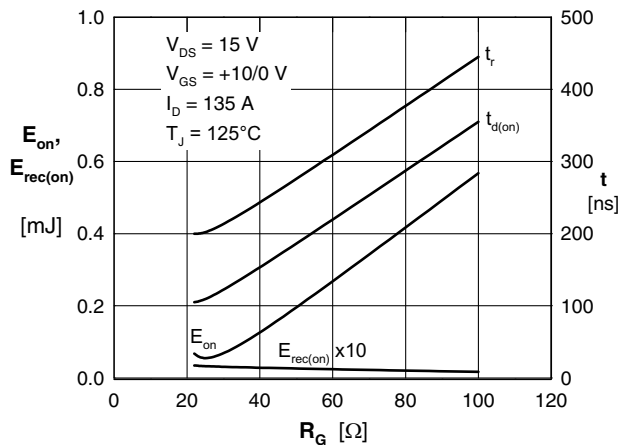


Fig. 11 Typ. turn-on energy & switching times vs. gate resistor, inductive switching

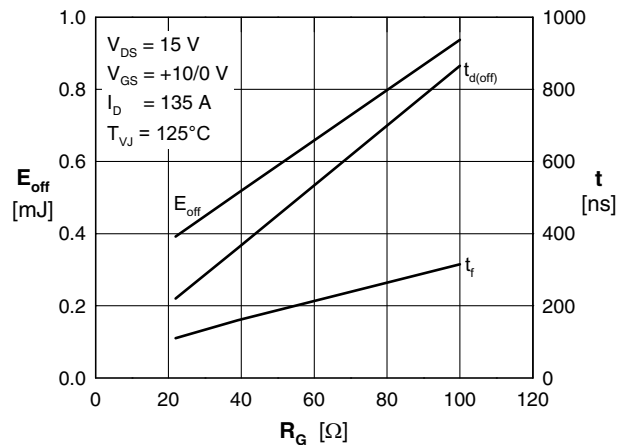


Fig. 12 Typ. turn-off energy & switching times vs. gate resistor, inductive switching

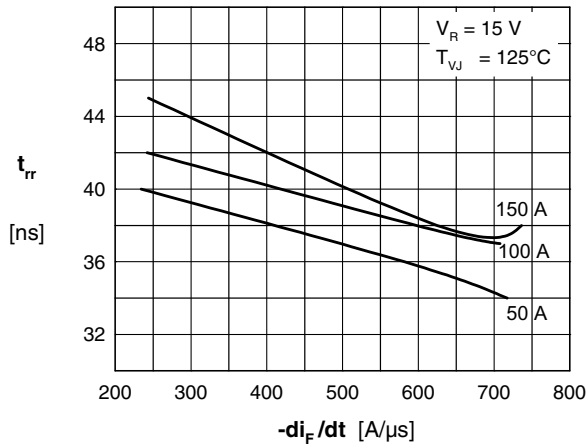


Fig. 13 Typ. reverse recovery time t_{rr} of the body diodes versus di/dt

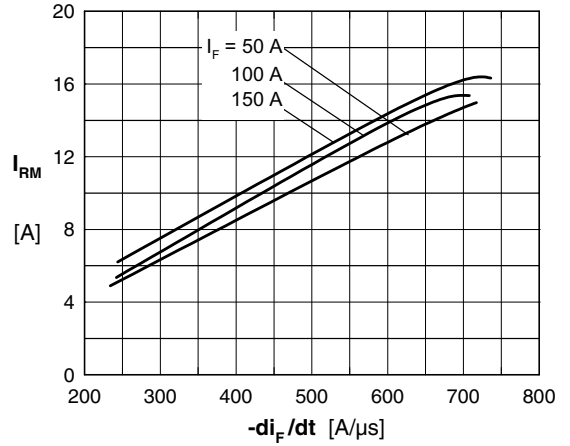


Fig. 14 Typ. reverse recovery current I_{RM} of the body diodes versus di/dt

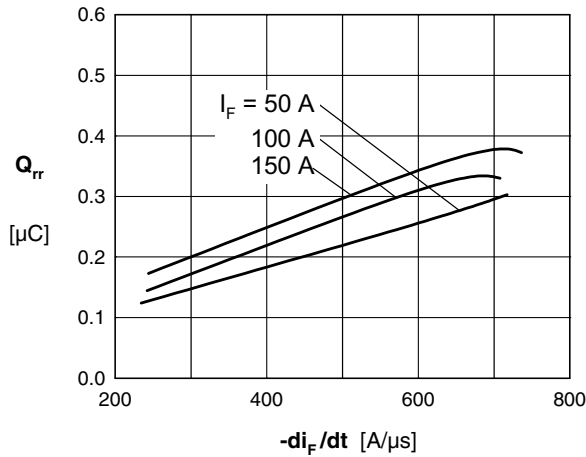


Fig. 15 Typ. reverse recovery charge Q_{rr} of the body diodes versus di/dt

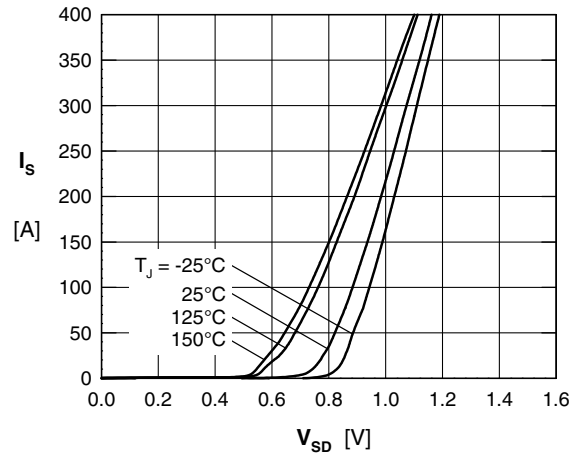


Fig. 16 Typ. source current I_s versus source drain voltage V_{SD} (body diode)

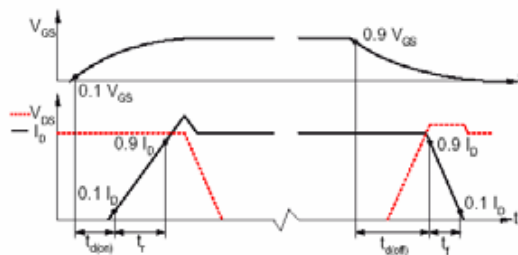


Fig. 17 Definition of switching times